

HVGT high voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

SHAPE DISPLAY:



FEATURES:

1. High reliability design.
2. High voltage design.
3. Low frequency .
4. Conform to RoHS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

SIZE: (Unit:mm)

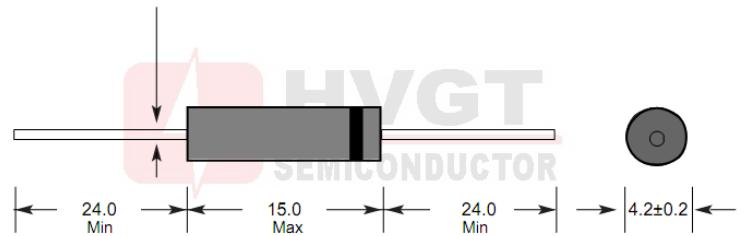
HVGT NAME: DO-415

APPLICATIONS:

1. High voltage multiplier circuit
2. High current and high voltage circuit.
3. General purpose high voltage rectifier.
4. Other .

DO-415 Series

Lead Diameter 0.8mm



Unit:mm

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 0.65 grams (approx).

MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Rense Voltage	V_{RRM}	$T_a=25^{\circ}C;$	8.0	kV
Average Output Current	I_F	$T_a=25^{\circ}C;$ Resistive Load	100	mA
Suege Current	I_{FSM}	$T_a=25^{\circ}C;$ 1/2 Sine(60Hz) ; 8.3mS	20	A
Junction Temperature	T_J		-40~+125	$^{\circ}C$
Allowable Operation Case Temperature	T_c		125	$^{\circ}C$
Storage Temperature	T_{STG}		-40~+125	$^{\circ}C$

ELECTRICAL CHARACTERISTICS: $T_a=25^{\circ}C$ (Unless otherwise specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_F	at $25^{\circ}C;$ $I_F = I_{F(AV)}$	10	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C;$ $V_R = V_{RRM}$	2.0	μA
	I_{R2}	at $100^{\circ}C;$ $V_R = V_{RRM}$	40	μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C;$ $I_F=0.5I_R;$ $I_R=I_{FAVM};$ $I_{RR}=0.25I_R$	--	nS
Junction Capacitance	C_J	at $25^{\circ}C;$ $V_R=0V;$ $f=1MHz$	--	pF



Fig 1

Forward Current Derating Curve

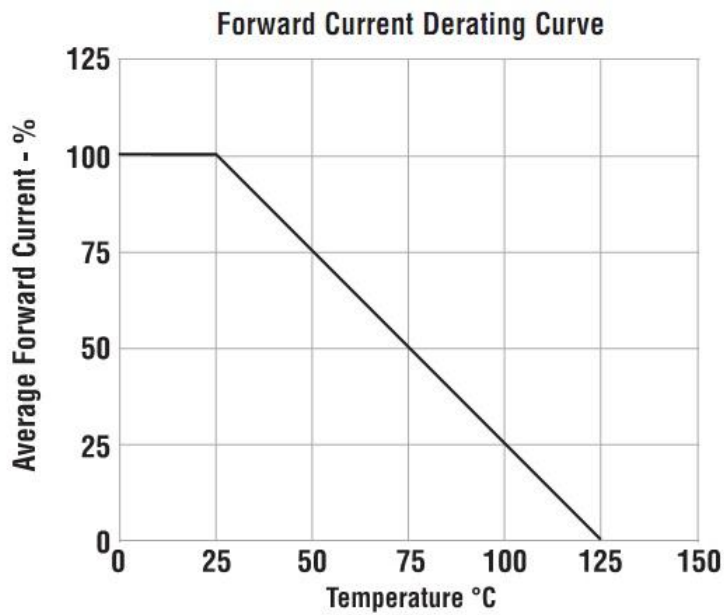
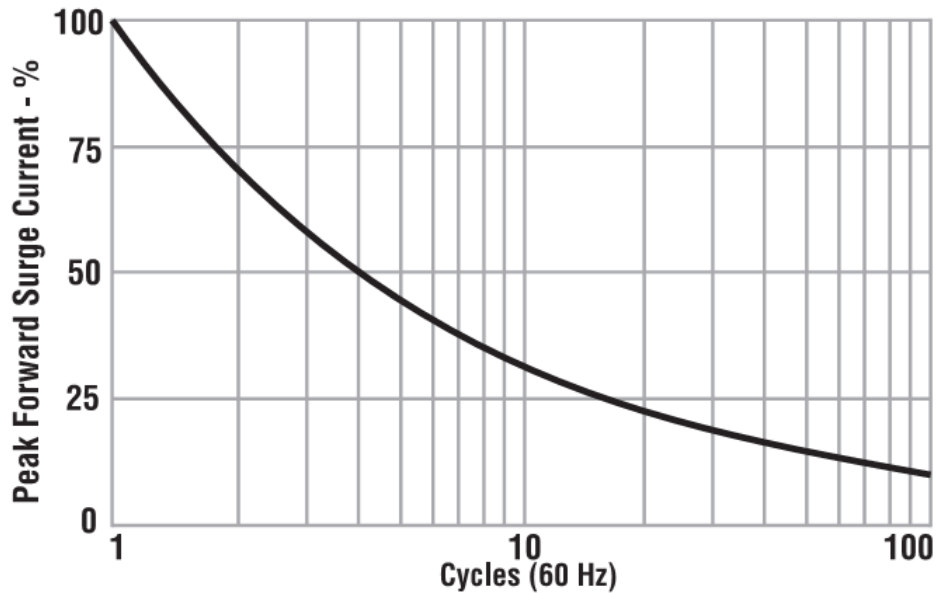


Fig 2

Repetitive Surge Current Derating Curve



This curve represents the percentage of published maximum surge rating as a function of surge repetition.

Marking	Type	Code	Cathode Mark
	2CL2F	2CL2F	